

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph at page 11, line 17, as follows:

These hydrocarbon groups in R⁷ and R⁸ may further have a substituent(s).
When the alkyl group R⁷ and R⁸ has a substituent, the substituted alkyl group is constituted by binding a ~~substituent~~ substituent and an ~~alkylene~~ alkylene group, and a monovalent non-metallic atomic group except a hydrogen atom is used as the substituent. Preferred examples of the monovalent groups include a halogen atom (F, Br, Cl, I), a hydroxyl group, an alkoxy group, an aryloxy group, a mercapto group, an alkylthio group, an arylthio group, an alkylidithio group, an arylidithio group, an amino group, an N-alkylamino group, an N,N-diarylamino group, an N-alkyl-N-arylamino group, an acyloxy group, a carbamoyloxy group, an N-alkylcarbamoyloxy group, an N-arylcarbamoyloxy group, an N,N-dialkylcarbamoyloxy group, an N,N-diarylcarbamoyloxy group, an N-alkyl-N-arylcarbamoyloxy group, an alkylsulfoxy group, an arylsulfoxy group, an acylthio group, an acylamino group, an N-alkylacylamino group, an N-acrylacylamino group, a ureido group, an N'-alkylureido group, an N',N'-dialkylureido group, an N'-arylureido group, an N',N'-diarylureido group, an N'-alkyl-N'-arylureido group, an N-alkylureido group, an N-arylureido group, an N'-alkyl-N-alkylureido group, an N'-alkyl-N-arylureido group, an N',N'-dialkyl-N-alkylureido group, N',N'-dialkyl-N-arylureido group, an N'-aryl-N-alkylureido group, an N'-aryl-N-arylureido group, an N',N'-diaryl-N-alkylureido group, an N',N'-diaryl-N-arylureido group, an N'-alkyl-N'-aryl-N-alkylureido group, an N'-alkyl-N'-aryl-N-arylureido group, an alkoxycarbonylamino group, an aryloxycarbonylamino group, an N-alkyl-N-alkoxycarbonylamino group, an N-alkyl-N-aryloxycarbonylamino group, an N-aryl-N-alkoxycarbonylamino group, an N-aryl-N-aryloxycarbonylamino

group, a formyl group, an acyl group, a carboxyl group, an alkoxycarbonyl group, an aryloxy carbonyl group, a carbamoyl group, an N-alkylcarbamoyl group, an N-dialkylcarbamoyl group, an N-arylcarbamoyl group, an N,N-diarylcarbamoyl group, an N-alkyl-N-arylcarbamoyl group, an alkylsulfinyl group, an arylsulfinyl group, an alkylsulfonyl group, an arylsulfonyl group, a sulfo group ($-\text{SO}_3\text{H}$) and a conjugate base group thereof (hereinafter referred to as "a sulfonato group"), an alkoxysulfonyl group, an arylsulfonyl group, a sulfinamoyl group, an N-alkylsulfinamoyl group, an N,N-dialkylsulfinamoyl group, an N-arylsulfinamoyl group, an N,N-diarylsulfinamoyl group, an N-alkyl-N-arylsulfinamoyl group, a sulfamoyl group, an N-alkylsulfamoyl group, N,N-dialkylsulfamoyl group, an N-arylsulfamoyl group, an N,N-diarylsulfamoyl group, an N-alkyl-N-arylsulfamoyl group, a phosphono group ($-\text{PO}_3\text{H}_2$) and a conjugate base group thereof (hereinafter referred to as "a phosphonato group"), a dialkylphosphono group ($-\text{PO}_3(\text{alkyl})_2$), a diarylphosphono group ($-\text{PO}_3(\text{alkyl})_2$), an alkylarylphosphono group ($-\text{PO}_3(\text{alkyl})(\text{aryl})$), a monoalkylphosphono group ($-\text{PO}_3\text{H}(\text{alkyl})$) and a conjugate base group thereof (hereinafter referred to as "an alkylphosphonato group"), a monoarylphosphono group ($-\text{PO}_3\text{H}(\text{aryl})$) and a conjugate base group thereof (hereinafter referred to as "an arylphosphonato group"), a phosphonoxy group ($-\text{OPO}_3\text{H}_2$) and a conjugate base group thereof (hereinafter referred to as "a phosphonatoxy group"), a dialkylphosphonoxy group ($-\text{OPO}_3(\text{alkyl})_2$), a diarylphosphonoxy group ($-\text{OPO}_3(\text{aryl})_2$), an alkylarylphosphonoxy group ($-\text{OPO}_3(\text{alkyl})(\text{aryl})$), a monoalkylphosphonoxy group ($-\text{OPO}_3\text{H}(\text{alkyl})$) and a conjugate base group thereof (hereinafter referred to as "an alkylphosphonatoxy group"), a monoarylphosphonoxy group ($-\text{OPO}_3\text{H}(\text{aryl})$) and a conjugate base group thereof (hereinafter referred to as

"an arylphosphonatoxy group), a cyano group, a nitro group, an aryl group, an alkenyl group and an alkynyl group.

Please amend the paragraph at page 15, line 24, as follows:

Further, the monovalent group as R⁷ and R⁸ each may be a substituted alkyl group. Examples of an alkylene moiety in such a substituted alkyl group include divalent organic residues formed by removing one hydrogen atom from each of the C1-20 alkyl groups as recited above, preferably C1-12 straight-chain alkylene groups, C3-12 branched alkylene groups and C5-10 cycloalkylene groups. Suitable examples of a substituted alkyl group formed by combining a substituent and an alkylene group include chloromethyl, bromomethyl, 2-chloroethyl, trifluoromethyl, methoxymethyl, methoxyethoxyethyl, allyloxymethyl, phenoxymethyl, methylthiomethyl, tolylthiomethyl, ethylaminoethyl, diethylaminopropyl, morpholinopropyl, acetyloxymethyl, benzoyloxymethyl, N-cyclohexylcarbamoyloxyethyl, N-phenylcarbamoyloxyethyl, acetylaminoethyl, N-ethylbenzoylaminopropyl, 2-hydroxyethyl, 2-hydroxypropyl, carboxypropyl, methoxycarbonyl ethyl, allyloxycarbonylbutyl, chlorophenoxycarbonylmethyl, carbamoylmethyl, N-methylcarbamoyl ethyl, N,N-dipropyl-carbamoylmethyl, N-(methoxyphenyl)carbamoyl ethyl, N-methyl-N-(sulfophenyl)carbamoylmethyl, sulfobutyl, sulfonatobutyl, sulfamoylbutyl, N-ethylsulfamoylmethyl, N,N-dipropylsulfamoylpropyl, N-tolylsulfamoylpropyl, N-methyl-N-(phosphonophenyl)sulfamoyloctyl, phosphonobutyl, phosphonato hexyl, diethylphosphonobutyl, diphenylphosphono-propyl, methylphosphonobutyl, methylphosphonatobutyl, triphosphono hexyl, tolylphosphonato hexyl, phosphonoxy-

propyl, phosphonatooxybutyl, benzyl, ~~phenethyl~~ phenethyl α -methylbenzyl, 1-methyl-1-phenylethyl, p-methylbenzyl, cinnamyl, allyl, 1-propenylmethyl, 2-butenyl, 2-methylallyl, 2-methyl-propenylmethyl, 2-propenyl, 2-butynyl and 3-butynyl groups.

Please amend the paragraph at page 55, line 22, as follows:

Specific examples of the acid generator include onium salts such as: the diazonium salts described in S.I. Schlesinger, *Photogr. Sci. Eng.*, 18, 387 (1974) and T.S. Bal et al., *Polymer*, 21, 423 (1980); the ammonium salts described in U.S. Patents 4,069,055 and 4,069,056 and Japanese Patent Laid-Open No. 140,140/1991; the phosphonium salts described in D.C. Necker et al., *Macromolecules*, 17, 2468 (1984), C.S. Wen et al., *Tech. Proc. Conf. Rad. Curing ASIA*, p.478 Tokyo, Oct. (1988), and U.S. Patents 4,069,055 and 4,069,056; the iodonium salts described in J.V. Crivello et al., ~~Macromolecules~~ Macromolecules 10 (6), 1307 (1977), *Chem. & Eng. News*, Nov. 28, p.31 (1988), European Patent 104,143, U.S. Patents 339,049 and 410,201, and Japanese Patent Laid-Open Nos. 150,848/1990 and 296,514/1990; the sulfonium salts described in J.V. Crivello et al., *Polymer J.*, 17, 73 (1985), J.V. Crivello et al., *J. Org. Chem.*, 43, 3055 (1978), W.R. Watt et al., *J. Polymer Sci., Polymer Chem. Ed.*, 22, 1789 (1984), J.V. Crivello et al., *Polymer Bull.*, 14, 279 (1985), J.V. Crivello et al., *Macromolecules*, 14 (5), 1141 (1981), J.V. Crivello et al., *J. Polymer Sci., Polymer Chem. Ed.*, 17, 2877 (1979), European Patent 370,693, U.S. Patent 3,902,114, ~~European~~ European Patents 233,567, 297,443, and 297,442, U.S. Patents 4,933,377, 410,201, 339,049, 4,760,013, 4,734,444, and 2,833,827, and German Patents 2,904,626, 3,604,580, and 3,604,581; the selenonium salts described in J.V. Crivello et al.,

Macromolecules, 10 (6), 1307 (1977) and J.V. Crivello et al., *J. Polymer Sci., Polymer Chem. Ed.*, 17, 1047 (1979); and the arsonium salts described in C.S. Wen et al., *Tech. Proc. Conf. Rad. Curing ASIA*, p.478 Tokyo, Oct. (1988). Examples thereof further include the organohalogen compounds described in U.S. Patent 3,905,815, Japanese Patent Publication No. 4605/1971, and Japanese Patent Laid-Open Nos. 36281/1973, 32070/1980, 239736/1985, 169835/1986, 169837/1986, 58241/1987, 212401/1987, 70243/1988, and 298339/1988; the organometallic compound/organic halide combinations described in K. Meier et al., *J. Rad. Curing*, 13 (4), 26 (1986), T.P. Gill et al., *Inorg. Chem.*, 19, 3007 (1980), D. Astruc, *Acc. Chem. Res.*, 19 (12), 377 (1986), and Japanese Patent Laid-Open No. 161445/1990; the photo-acid generators having an o-nitrobenzyl type protective group described in S. Hayase et al., *J. Polymer Sci.*, 25, 753 (1987), E. Reichman et al., *J. Polymer Sci., Polymer Chem. Ed.*, 23, 1 (1985), Q.Q. Zhu et al., *J. Photochem.*, 36, 85, 39, 317 (1987), B. Amit et al., *Tetrahedron Lett.*, (24) 2205 (1973), D.H.R. Barton et al., *J. Chem Soc.*, 3571 (1965), P.M. Collins et al., *J. Chem. Soc., Perkin I*, 1695 (1975), M. Rudinstein et al., *Tetrahedron Lett.*, (17), 1445 (1975), J.W. Walker et al., *J. Am. Chem. Soc.*, 110, 7170 (1988), S.C. Busman et al., *J. Imaging Technol.*, 11 (4), (1985), H.M. Houlihan et al., *Macromolecules*, 21, 2001 (1988), P.M. Collins et al., *J. Chem. Soc., Chem. Commun.*, 532 (1972), S. Hayase et al., *Macromolecules*, 18, 1799 (1985), E. Reichmanis et al., *J. Electrochem. Soc., Solid State Sci. Technol.*, 130 (6), F.M. Houlihan et al., *Macromolecules*, 21, 2001 (1988), European Patents 0,290,750, 046,083, 156,535, 271,851, and 0,388,343, U.S. Patents 3,901,710 and 4,181,531, and Japanese Patent Laid-Open Nos. 198538/1985 and 133022/1978; compounds which photodecompose to generate a sulfonic acid and are represented

by the iminosulfonates and the like described in Tunooka et al., *Polymer Preprints*, Japan, 35 (8), G. Berner et al., *J. Rad. Curing*, 13 (4), W.J. Mijs et al., *Coating Technol.*, 55 (697), 45 (1983), Akzo, H. Adachi et al., *Polymer Preprints*, Japan, 37 (3), European Patents 0,199,672, 84,515, 199,672, 044,115, and 0,101,122, U.S. Patents 4,618,554, 4,371,605, and 4,431,774, and Japanese Patent Laid-Open Nos. 18143/1989, 245756/1990, and 140109/1991; and the disulfone compounds described in Japanese Patent Laid-Open No. 166544/1986.

Please amend the paragraph at page 84, line 10, as follows:

The positive type lithographic printing plate precursor of Example 8 thus obtained was exposed to a PS light through a step guide manufactured by Fuji Photo Film Co., Ltd., and then processed by an automatic processor containing developer DP-4 (1:8), manufactured by Fuji Photo Film Co., Ltd. Subsequently, printing was conducted with ~~Heidel~~ Heidelberg printing press KOR-D. As a result, 5,000 satisfactory printed sheets were obtained in which the nonimage areas were free from soils.

Please amend the paragraph at page 87, line 1, as follows:

[Composition of Image-Forming Layer]

A composition consisting of 0.1 g of IRG22 (IR dye manufactured by Nippon Kayaku Co., Ltd.), 0.21 g of the crosslinking agent A, 2.1 g of a phenol-formaldehyde novolac (weight-average molecular weight, 12,000), 0.02 g of diphenyliodonium 9,10-dimethoxyanthracenesulfonate, 0.06 g of Megafac Megafac F-176 (fluorochemical surfactant manufactured by Dainippon Ink & Chemicals, Inc.), 15 g of

methyl ethyl ketone, and 12 g of 2-methoxy-1-propane was applied to the same support as in the Examples given above. Thus, a negative type heat-sensitive lithographic printing plate precursor of Example 13 was obtained.

Please amend the paragraph at page 87, line 13, as follows:

The negative type lithographic printing plate precursor of Example 13 thus obtained was exposed with a semiconductor laser (wavelength, 825 nm; beam diameter, $1/e^2 = 6 \mu\text{m}$) as a heat mode laser at a linear velocity of 8 m/sec and a plate surface output of 110 mW. After the exposure, the printing plate precursor was heat-treated at 110°C for 1 minute and then processed by an automatic processor containing developer DP-4 (1:8) and rinse FR-3 (1:7), both manufactured by Fuji Photo Film Co., Ltd. Subsequently, the plate surface was treated with gum GU-7 (1:1), manufactured by Fuji Photo Film Co., Ltd. Printing was conducted with ~~Heidel~~ Heidelberg printing press KOR-D. As a result, 6,000 printed sheets were obtained in which the nonimage areas were free from soils.